4-/8-Channel Wideband Video Multiplexers

Features

- Wide Bandwidth: 500 MHz
- Very Low Crosstalk: -97 dB @ 5 MHz
- On-Board TTL-Compatible Latches with Readback
- Optional Negative Supply
- Low r_{DS(on)}: 45 Ω

Benefits

- Improved System Bandwidth
- Improved Channel Off-Isolation
- Simplified Logic Interfacing
- Allows Bipolar Signal Swings
- Reduced Insertion Loss
- Allows Differential Signal Switching

Applications

- Wideband Signal Routing and Multiplexing
- Video Switchers
- ATE Systems
- Infrared Imaging

Description

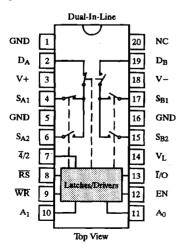
The DG534 is a digitally selectable 4-channel or dual 2-channel multiplexer. The DG538 is an 8-channel or dual 4-channel multiplexer. On-chip TTL-compatible address decoding logic and latches with data readback are included to simplify the interface to a microprocessor data bus. The low on-resistance and low capacitance of the these devices make them ideal for wideband data multiplexing and video and audio signal routing in channel selectors and crosspoint arrays. An optional negative supply pin allows the handling of bipolar signals without dc biasing.

The DG534/DG538 are built on a D/CMOS process that combines n-channel DMOS switching FETs with low-power CMOS control logic, drivers and latches. The low-capacitance DMOS FETs are in a "T" configuration to achieve extremely high levels of off isolation. Crosstalk is reduced to -97 dB at 5 MHz by including a ground line between each adjacent signal path.

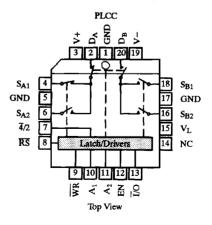
The DG534A/DG538A are recommended for new designs.

Functional Block Diagrams and Pin Configurations

DG534DJ



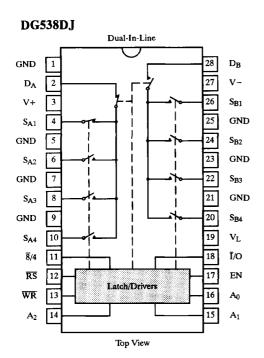
DG534DN

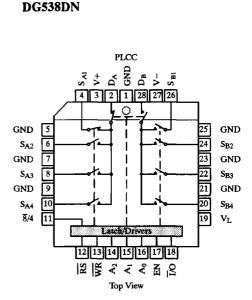


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Functional Block Diagrams and Pin Configurations (Cont'd)





Truth Tables and Ordering Information

Ordering Information - DG534

	B	
Temp Range	Package	Part Number
-40 to 85°C	20-Pin Plastic DIP	DG534DJ
-40 to 85°C	20-Pin PLCC	DG534DN
−55 to 125°C	20-Pin Sidebraze	DG534AP
-33 to 123 C	20-1 iii Sideoraze	DG534AP/883

Truth Table — DG534

ĪΟ	A ₁	A ₀	EN	WR	RS	4/2*	On Switch						
х	х	х	х	5	1	1	Maintains previous state None (latches cleared)						
X	X	Х	х	X	0	Х							
Х	Х	Х	0	0	1	Х	None	·	Ī				
0	0	0	1	0	1	0	S _{A1}	D. and D-	7				
0	0	1	1	0	1	0	S _{A2}	D _A and D _B may be	L .				
0	1	0	1	0	1	0	S _{B1}	connected	Latches Transparent				
0	1	1	1	0	1	0	S _{B2}	externally	Trumparoni				
0	Х	0	1	0	1	1	S _{A1} a	and S _{B1}	7				
0	Х	1	1	0	1	1 .	S _{A2} 8	and S _{B2}	7				
1		Note b		1	1	Note c							

Logic "0" = $V_{AL} \le 0.8 \text{ V}$ Logic "1" = $V_{AH} \ge 2 \text{ V}$

X = Don't Care

Notes:

- a. Connect DA and DB together externally for single-ended operation.
- With I/O high, An pin becomes output and reflects latch contents. See timing diagrams for more detail.
- c. 4/2 can be either "1" or "0" but should not change during these operations.



Truth Tables and Ordering Information (Cont'd)

Ordering Information - DG538

Temp Range	Package	Part Number		
40 to 950C	28-Pin Plastic DIP	DG538DJ		
−40 to 85°C	28-Pin PLCC	DG538DN		
55 to 1259C	28-Pin Sidebraze	DG538AP		
−55 to 125°C	20-rin Sideoraze	DG538AP/883		

Truth	Table	_	DG538
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ĬΟ	A ₂	Aı	Αŋ	EN	WR	RS	8/4ª	On Switch Maintains previous state None (latches cleared) None						
Х	х	х	х	х	7	1	1	<u> </u>						
X	X	Х	Х	Х	Х	0	Х	 						
Х	Х	Х	Х	0	0	1	X	None						
0	0	0	0	1	0	1	0	S _{A1}		1				
0	0	0	1	1	0	1	0	S _{A2}						
0	0	1	0	1	0	1	0	S _{A3}	D _A and D _B	i				
0	0	1	1	1	0	1	0	S _{A4}	should be					
0	1	0	0	1	0	1	0	S _{B1}		Latabas				
0	1	0	1	1	0	1	0	S _{B2}	connected externally Latches Transparen	Transparent				
0	1	1	0	1	0	1	0	S _{B3}						
0	1	1	1	1	0	1	0	S _{B4}		,				
0	X	0	0	1	0	1	1	S _{A1} a	ind S _{B1}]				
0	Х	0	1	1	0	1	1	S _{A2} a	ind S _{B2}]				
0	Х	1	0	1	0	1	1	S _{A3} a	ind S _{B3}]				
0	Х	1	1	1	0	1	1	S _{A4} a	ınd S _{B4}					
1		No	te b		1	1	Note c							

Logic "0" = $V_{AL} \le 0.8 \text{ V}$ Logic "1" = $V_{AH} \ge 2 V$ X = Don't Care

- a. Connect D_A and D_B together externally for single-ended operation. b. With I/O high, A_n pin becomes output and reflects latch contents. See timing diagrams for more detail.

 c. 8/4 can be either "1" or "0" but should not change during these operations.

Absolute Maximum Ratings

	V+ to GND
	V+ to V0.3 V to +21 V
٠	V- to GND
•	$V_L - \dots = 0 V \text{ to } (V+) + 0.3 V$
	Digital Inputs (V-) -0.3 V to (V+) + 0.3 V
	or 20 mA, whichever occurs first
•	$V_{S}, V_{D} \dots (V-) -0.3 V \text{ to } (V-) + 14 V$
	or 20 mA, whichever occurs first
•	Current (any terminal) Continuous
•	Current(S or D) Pulsed I ms 10% Duty

Storage Temperature	(A Suffix)65 to 150°C (D Suffix)65 to 125°C
PLCC ^c	'

Notes:

- a. All leads soldered or welded to PC board.
- b. Derate 8.3 mW/°C above 75°C.
- c. Derate 6 mW/°C above 75°C.
- d. Derate 16 mW/°C above 75°C.

DG534/538



Specifications^a

		Test Conditions Unless Otherwise Spe				A Suffix -55 to 125°C		D Suffix -40 to 85°C		
Parameter	Symbol	$V + = 15 \text{ V}, V - = -3 \text{ V}, V_L = 5 \text{ V} \overline{\text{WR}} = 0.8 \text{ V}, \overline{\text{RS}}, \text{EN} = 2 \text{ V} $ Temp	Temp ^b	Турс	Mind	Maxd	Min ^d	Maxd	Unit	
Analog Switch										
Analog Signal Rangeg	VANALOG	V- = -5 V		Full		-5	8	-5	8	v
Drain-Source On-Resistance	r _{DS(on)}	$I_S = -10 \text{ mA}, V_S = 0$		Room Full	45		90 120		90 120	Ω
Resistance Match Between Channels	$\Delta r_{DS(on)}$	V _{AIL} = 0.8 V, V _{AIH} = 2 V Sequence Each Switch On		Room			9		9	\$2
Source Off Leakage Current	I _{S(off)}	$V_S = 8 \text{ V}, V_D = 0 \text{ V}, EN = 0.8 \text{ V}$		Room Full	0.05	-5 -50	5 50	-5 -50	5 50	
Drain Off Leakage Current	I _{D(off)}	$V_S = 0 \text{ V}, V_D = 8 \text{ V}, \text{EN}$	= 0.8 V	Room Full	0.1	-20 -500	20 500	-20 -100	20 100	пA
Drain On Leakage Current	I _{D(on)}	$V_S = V_D = 8 V$	$V_S = V_D = 8 V$		0.1	-20 -1000	20 1000	-20 -200	20 200	
Digital Control										
Input Voltage High	V _{AIH}			Full		2		2		
Input Voltage Low	V _{AIL}			Fuli			0.8		0.8	v
Address Input Current	I _{AI}	$V_{AI} = 0 \text{ V}, \text{ or } 2 \text{ V or } 5 \text{ V}$		Room Full	-0.1	-1 -10	1 10	-1 -10	1 10	μА
Address Output Current	I _{AO}	$V_{AO} = 2.7 \text{ V}$	Room	-300						
Address Odipat Carrent	IAO	$V_{AO} = 0.4 \text{ V}$	$V_{AO} = 0.4 \text{ V}$ Room		300					
Dynamic Characteristic	:5							. 199		
On State Input	C		PLCC	Room	28		40		40	
Capacitanceg	C _{S(on)}		DIP	Room	31	_		_		
Off State Input					31		45		45	
	Ceroffi		PLCC	Room	3		45 5		45	nF
Capacitance ^g	C _{S(off)}		DIP	Room Room	3					pF
Capacitance [§] Off State Output	-		DIP	Room Room	3 4 6				5 8	pF
Capacitance ^g	C _{S(off)}		DIP	Room Room Room	3 4 6 8		10		4 5 8 10	pF
Capacitance [§] Off State Output	-		DIP	Room Room	3 4 6		5		5 8	pF
Capacitance ^g Off State Output Capacitance ^g	C _{D(off)}		DIP	Room Room Room Room	3 4 6 8	50 25	10	50 25	4 5 8 10 300	
Capacitance [§] Off State Output Capacitance [§] Transition Time Break-Before-Make	C _{D(off)}		DIP	Room Room Room Room Room Full Room	3 4 6 8 170		10		4 5 8 10 300	pF
Capacitance [§] Off State Output Capacitance [§] Transition Time Break-Before-Make Interval	C _{D(off)} trans topen		DIP	Room Room Room Room Full Room Full Room	3 4 6 8 170		5 10 300 500		4 5 8 10 300 500	
Capacitance ^k Off State Output Capacitance ^k Transition Time Break-Before-Make Interval EN, WR Turn On Time EN, Turn Off Time	C _{D(off)} ttrans topen ton		DIP	Room Room Room Room Room Full Room Full Room Full Room Full Room	3 4 6 8 170 80		300 500 300 500		4 5 8 10 300 500	
Capacitance Off State Output Capacitance Transition Time Break-Before-Make Interval EN, WR Turn On Time	CD(off) tTRANS tOPEN tON	$R_{L} = 75 \Omega, f = 5 \text{ MHz}$ $EN = 0.8 \text{ V}$	DIP PLCC DIP	Room Room Room Room Room Full Room Full Room Full Room Full Room Full Room Full	3 4 6 8 170 80 180 95 -70 -75		300 500 300 500		4 5 8 10 300 500	ns
Capacitance [§] Off State Output Capacitance [§] Transition Time Break-Before-Make Interval EN, WR Turn On Time EN, Turn Off Time Charge Injection	CD(off) ttrans topen ton toff	EN = 0.8 V	DIP PLCC DIP	Room Room Room Room Room Room Full Room Full Room Full Room Full Room Full Room Full Room	3 4 6 8 170 80 180 95 -70 -75 -65		300 500 300 500		4 5 8 10 300 500	ns
Capacitancek Off State Output Capacitancek Transition Time Break-Before-Make Interval EN, WR Turn On Time EN, Turn Off Time Charge Injection Chip Disabled Crosstalkf	CD(off) ttrans topen ton toff Qi Xtalk(CD)		DIP PLCC DIP	Room Room Room Room Room Room Full Room Full Room Full Room Full Room Room Room Room	3 4 6 8 170 80 180 95 -70 -75		300 500 300 500		4 5 8 10 300 500	ns
Capacitance [§] Off State Output Capacitance [§] Transition Time Break-Before-Make Interval EN, WR Turn On Time EN, Turn Off Time Charge Injection	CD(off) ttrans topen ton toff	$EN = 0.8 \text{ V}$ $R_{IN} = 10 \Omega, R_L = 10 \text{ k}\Omega$	PLCC DIP PLCC PLCC PLCC	Room Room Room Room Room Room Full Room Full Room Full Room Full Room Full Room Full Room	3 4 6 8 170 80 180 95 -70 -75 -65 -97		300 500 300 500		4 5 8 10 300 500	ns pC



Specifications^a

		Test Conditions Unless Otherwise Specified					uffix 125°C	D Suffix -40 to 85°C		
Parameter	Symbol	V + = 15 V, V - = -3 V, V $\overline{WR} = 0.8 \text{ V}, \overline{RS}, EN =$	V _L = 5 V 2 V	Temp ^b	Турс	Min ^d	Max ^d	Mind	Max ^d	Unit
Dynamic Characteristic	es (Cont'd)									
		$R_{IN} = 10 \Omega, R_L = 10 \text{ k}\Omega$ f = 5 MHz	PLCC	Room	-77					
All YT- all Commands			DIP	Room	-72					
All Hostile Crosstalk	X _{TALK(AH)}	$R_{IN} = 75 \Omega$, $R_L = 75 \Omega$	PLCC	Room	-77					
		f = 5 MHz	DIP	Room	-72					dΒ
Diff and I Constalls	v	$R_{IN} = 10 \Omega, R_L = 10 k\Omega$ $f = 5 \text{ MHz}$ $R_{IN} = R_L = 75 \Omega$ $f = 5 \text{ MHz}$		Room	-84					
Differential Crosstalk	X _{TALK(DIFF)}			Room	84					
Bandwidth	BW	$R_L = 50 \Omega$	Room	500					MHz	
Power Supplies										
Positive Supply Current	I+	Any One Channel Selected with		Room Full	0.6		2 5		2 5	
Negative Supply Current	I-	Address Inputs at GND		Room Full	0.6	-1.8 -2		-1.8 -2		mA
Functional Check of	V+ to V-			· Full		10	21	10	21	v
Maximum Operating	V- to GND	Functional Test Oni	Full		-5.5	0	-5.5	0		
Supply Voltage Range	V+ to GND	1	Full		10	21	10	21		
Logic Supply Current	I _L			Full	150	.	500		500	μА
Timing										
Reset to Write	t _{RW}			Full		50		50		
WR, RS Minimum Pulse Width	t _{MPW}			Full		200		200		
A ₀ , A ₁ , EN Data Valid to Strobe	t _{DW}			Fuli		100		100		1
A ₀ , A ₁ , EN Data Valid after Strobe	t _{WD}	See Figure 1		Full		50		50		ns
Address Bus Tri-State ^e	t _{AZ}	1		Room	25					[
Address Bus Output	t _{AO}	1		Room	95					[
Address Bus Input	tAI	1		Room	110	İ				1

- Notes:

 Refer to PROCESS OPTION FLOWCHART (Section 5 of the 1994 Data Book or FaxBack number 7103).

 Room = 25°C, Full = as determined by the operating temperature suffix.

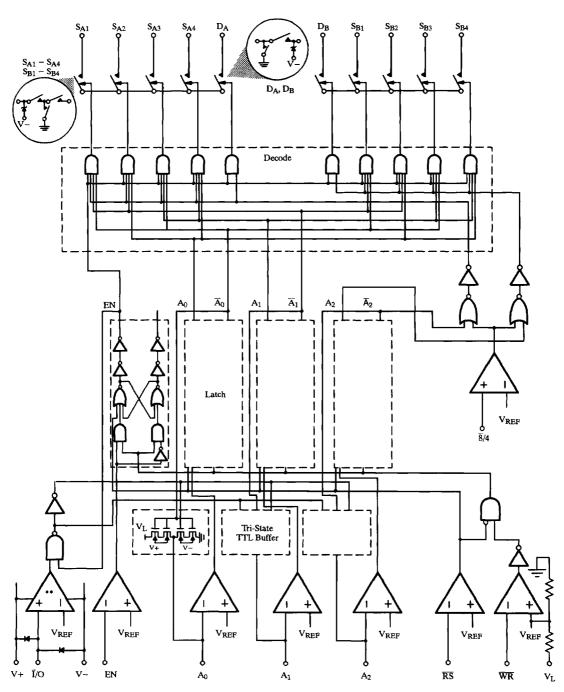
 Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

 The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Defined by system bus requirements.

 f. Each individual pin shown as GND must be grounded.
- g. Guaranteed by design, not subject to production test.

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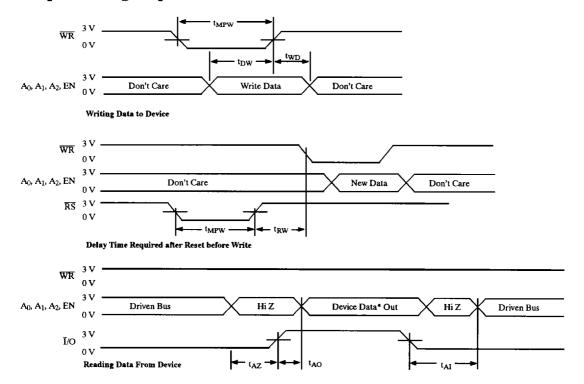
Control Circuitry



^{*} Decode section includes delay circuitry in AND gating to ensure proper break-before-make operation.

** Typical all digital inputs.

Output Timing Requirements



^{*} Enable must be latched high to read data, otherwise BUS is high Z. V - ≤ -3 V required for readback functionality.

Figure 1.

Applications

To protect against latchup V_L must not exceed V+ by more than 0.3 V. This is easily achieved by generating V_L from V + using a Zener or a resistor divider network as shown in Figure 2. When an external V_L is available the alternative

simple protection circuit shown in Figure 3 should be used to prevent triggering the parasitic SCR during power up. The DG53XA does not require these protection diodes.

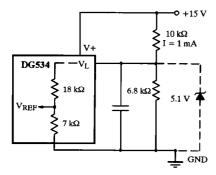


Figure 2. V_L Generated from V+

